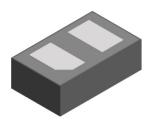


PESDMC2FD5VBHF

Bi-directional 5V Low Capacitance ESD Protector

Description

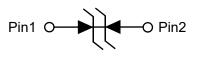
The PESDMC2FD5VBHF protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

Feature

- 80W peak pulse power per line (t_P = 8/20µs)
- DFN1006-2L package
- Response time is typically < 1 ns</p>
- Bidirectional configurations
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30kV(air), ± 30kV(contact); IEC 61000-4-5 (Lightning) 8.5A (8/20us)



Circuit Diagram



Marking (Top View)

Applications

- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals

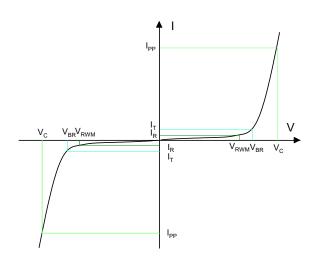
Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating

PESDMC2FD5VBHF

Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _c	Clamping Voltage @ I _{PP}		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	V _F Forward Voltage @ I _F		



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	-	-	-	5	V
Breakdown Voltage	V _{BR}	I _t = 1mA	7	-	-	V
Reverse Leakage Current	I _R	V _{RWM} = 5V	-	-	1	μA
Clamping Voltage ¹⁾	V _c	TLP = 16A, t _p = 100ns	-	10	-	V
Dynamic resistance ¹⁾	R _{DYN}	-	-	0.15	-	Ω
Clamping Voltage ²⁾	V _c	I _{PP} = 1A,t _P = 8/20μs	-	9.5	11	V
		I _{PP} = 8.5A,t _P = 8/20μs	-	10	12	V
Junction Capacitance	CJ	V _R = 0V,f = 1MHz	-	0.8	1.0	pF

Notes:

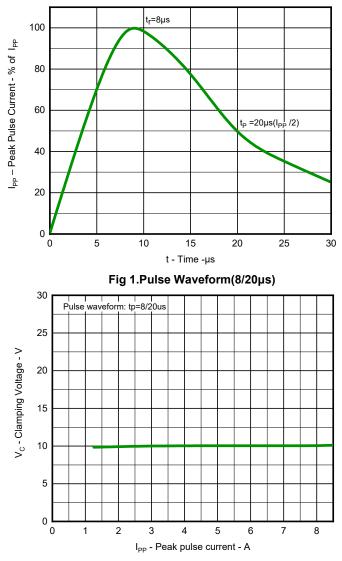
1.TLP parameter: $Z_0=50\Omega$, $t_p=100$ ns, $t_r=2$ ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A. 2.Non-repetitive current pulse, according to IEC61000-4-5.

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µs)	P _{PP}	80	W
Peak Pulse Current (t _P = 8/20µs)	I _{PP}	8.5	A
Lead Soldering Temperature	TL	260 (10 sec)	°C
Junction and Storage Temperature Range	T _{J,} T _{STG}	-55~+150	°C
ESD Protection-Contact Discharge	V _{ESD}	±30	kV
ESD Protection-Air Discharge	V _{ESD}	±30	kV

PESDMC2FD5VBHF

Typical Characteristics





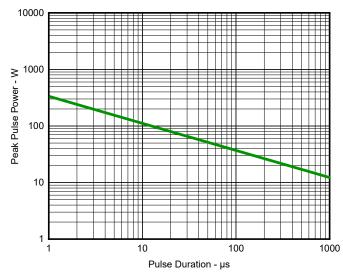
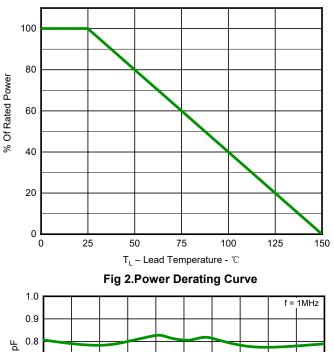
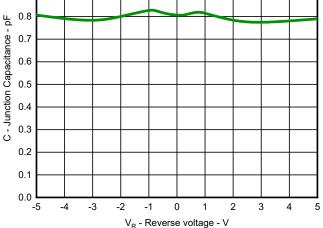


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time







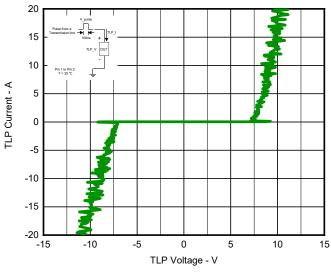


Fig 6. TLP Measurement

PESDMC2FD5VBHF

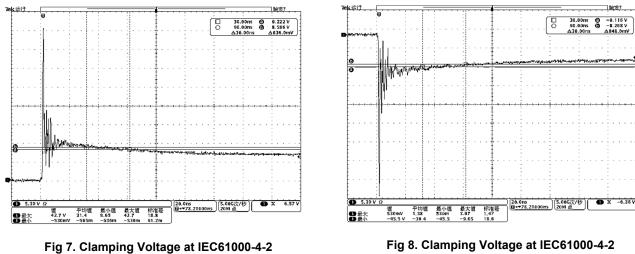
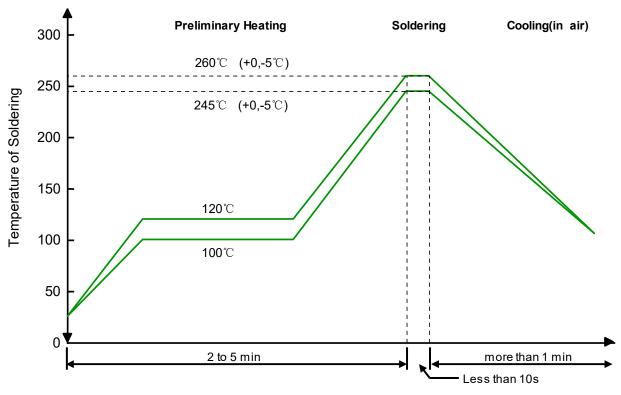


Fig 8. Clamping Voltage at IEC61000-4-2 -8kV Pulse Waveform

Solder Reflow Recommendation

+8kV Pulse Waveform



Remark: Pb free for 260°C; Pb for 245°C.

PESDMC2FD5VBHF

ESD Protector

PCB Design

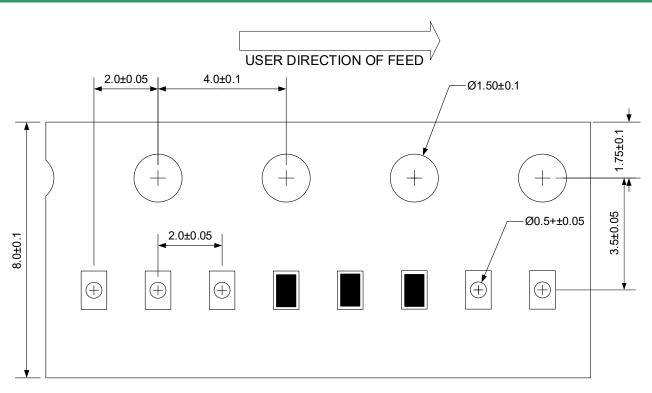
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- ➢ Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

Device Package		Package Reel	
PESDMC2FD5VBHF	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

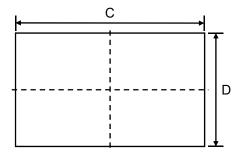
Load with information



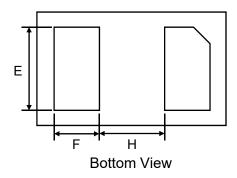
Unit:mm

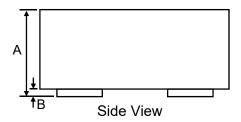
PESDMC2FD5VBHF

Product dimension (DFN1006-2L)

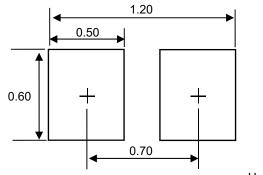








Dim	Millim	neters	Inches		
	Min	Max	Min	Max	
А	0.340	0.498	0.013	0.020	
В	0.000	0.050	0.000	0.002	
С	0.950	1.080	0.037	0.043	
D	0.550	0.680	0.022	0.027	
E	0.400	0.600	0.016	0.024	
F	0.200	0.300	0.008	0.012	
Н	0.400 Тур.		0.015 Typ.		



Unit:mm



IMPORTANT NOTICE

P and Prisemi are registered trademarks of Prisemi Electronics Co., Ltd (Prisemi), Prisemi reserves the right to make changes without further notice to any products herein. Prisemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Prisemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in Prisemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Prisemi does not convey any license under its patent rights nor the rights of others. The products listed in this document are designed to be used with ordinary electronic equipment or devices, Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

> Website: http://www.prisemi.com For additional information, please contact your local Sales Representative. ©Copyright 2009, Prisemi Electronics Prisemi®is a registered trademark of Prisemi Electronics. All rights are reserved.